

Form PTO-1.119	Doctor Number (Optional)	Atticution Number
O I P E INFORMATION DISCLOSURE CITATION IN AN APPLICATION	IME-03-009	10/767,275
APR 15 2004 <i>(Use several sheets if necessary)</i>	Inventor Ming Fu Li et al.	Filing Date 01/29/04

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	TITLE	CLASS	BOOK CLASS	NUMBER OF VOLUMES X NUMBER OF PAGES
			CLAS	BOOK CLAS	
O.N. 6208555	3/27/01	Noble	365	159	3/30/99
65122741	1/28/03	King et al.	257	369	6/22/00
6528370	3/4/03	Suzuki et al.	438	257	7/29/02
5466949	11/14/95	Okuno	257	25	8/4/94
56165154	1/1/97	Okuno	438	478	6/7/95
6239450	5/29/01	Harvey et al.	257	49	1/14/99
56061772	2/25/97	Wallace et al.	257	25	12/6/94
O.N. 6228555	3/27/01	Noble	365	159	3/30/99

FOREIGN PATENT DOCUMENTS

ON O/N	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
ON	EP 1 168456 A2	1/2/02	European Patent App.	H01L	29/788		
O/N	0 6686018 A2	5/19/94	European Patent App.	H01L	29/188		

OTHER DOCUMENTS (including Author, Title, Date, References Page, Etc.)

ON	-	L.L. Chang et al., "Resonant tunneling in the semiconductor double barriers," <i>Appl. Phys. Lett.</i> , Vol. 24, pp. 593-595, June 1974.
ON	-	I.P. Sun et al., "Resonant Tunneling Diodes: Models and Properties," <i>Proc. of the IEEE</i> , Vol. 86, No. 4, April 1998, pp. 648-661, (SIA).
ON	-	Ikeda et al., "Resonant tunneling characteristics in SiO_2/Si double barrier structures in a wide range of applied voltage," <i>Appl. Phys. Lett.</i> , Vol. 83, No. 7, Aug. 2003, pp. 1456-1458. DATE CONSIDERED
EXAMINER	ON	6/7/05.

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ON	-	Wong et al., "Self-Aligned (Top and Bottom) Double-Gate MOSFET with a 25 nm Thick Silicon Channel," 1997 IEDM Technical Digest, pp. 16.6.1 to 16.6.4.
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